# BLF644P

Broadband power LDMOS transistor Rev. 1 — 11 June 2013

**Objective data sheet** 

#### 1. **Product profile**

### **1.1 General description**

A 70 W LDMOS RF power transistor for broadcast transmitter and industrial applications. The transistor is suitable for the frequency range HF to 1300 MHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital applications.

#### Table 1. **Typical performance**

RF performance at  $T_{case} = 25 \ ^{\circ}C$  in a common source test circuit.

Test signal	f	$V_{DS}$	PL	Gp	$\eta_D$	IMD
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
CW, class-A	860	32	90	22	<tbd></tbd>	-
CW pulsed, class-AB	860	32	100	23.5	66	<tbd></tbd>
2-tone, class-AB	860	32	45	23	<tbd></tbd>	<tbd></tbd>

### 1.2 Features and benefits

- Integrated ESD protection
- Excellent ruggedness
- High power gain
- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Communication transmitter applications in the HF to 1300 MHz frequency range
- Industrial applications in the HF to 1300 MHz frequency range



#### Broadband power LDMOS transistor

## 2. Pinning information

Table 2.	Pinning			
Pin	Description		Simplified outline	Graphic symbol
1	drain1			
2	drain2			3 ≁
3	gate1			5
4	gate2		3 4 5	4 <b>→</b>  2
5	source	<u>[1]</u>		aaa-005775

[1] Connected to flange.

### 3. Ordering information

Table 3. Orde	ering inf	ormation	
Type number Package		je	
	Name	Description	Version
BLF644P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1228A

## 4. Limiting values

Table 4. In accorda	Limiting values nce with the Absolute Max	kimum Rating System (IE	EC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
V <sub>GS</sub>	gate-source voltage		-0.5	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

## 5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 90 W	[ <u>1]</u> <tbd></tbd>	K/W

[1]  $R_{th(j-c)}$  is measured under RF conditions.

Max Unit V

V

V

μΑ

-

2.4

2.5

1.4

Тур

1.9

2.0

-

-

#### **Characteristics** 6.

<b>Table 6.</b> $T_j = 25 \ ^{\circ}C$	DC characteristics ; per section unless otherwise spe	ecified.	
Symbol	Parameter	Conditions	Min
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS}$ = 0 V; $I_D$ = 0.5 mA	65
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 32 \text{ V}; \text{ I}_{D} = 50 \text{ mA}$	1.4
$V_{GSq}$	gate-source quiescent voltage	$V_{DS}$ = 32 V; $I_{Dq}$ = 250 mA	1.5
I <sub>DSS</sub>	drain leakage current	$V_{GS}$ = 0 V; $V_{DS}$ = 32 V	-
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$	-

I <sub>DSX</sub>	drain cut-off current	$\label{eq:VGS} \begin{array}{l} V_{GS} = V_{GS(th)} + 3.75 \; V; \\ V_{DS} = 10 \; V \end{array}$	-	9.0	-	А
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = ±10 V; $V_{DS}$ = 0 V	-	-	50	nA
<b>g</b> <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 2.5 A	-	3.3	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; I <sub>D</sub> = 1.75 A	-	300	-	mΩ

#### Table 7. **AC** characteristics

 $T_i = 25 \ ^{\circ}C$ ; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 32 V; f = 1 MHz	-	39	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 32 V; f = 1 MHz	-	15	-	pF
C <sub>rs</sub>	feedback capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 32 V; f = 1 MHz	-	0.84	-	pF

#### Table 8. **RF characteristics**

Test signal: CW pulsed, class-AB; f = 860 MHz; RF performance at V<sub>DS</sub> = 32 V; I<sub>Dq</sub> = 200 mA;  $T_{case} = 25 \, \circ C$ ; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L</sub> = 100 W	23	23.5	-	dB
$\eta_D$	drain efficiency	P <sub>L</sub> = 100 W	61	66	-	%
RL <sub>in</sub>	input return loss	P <sub>L</sub> = 100 W	-	-15	-10	dBc

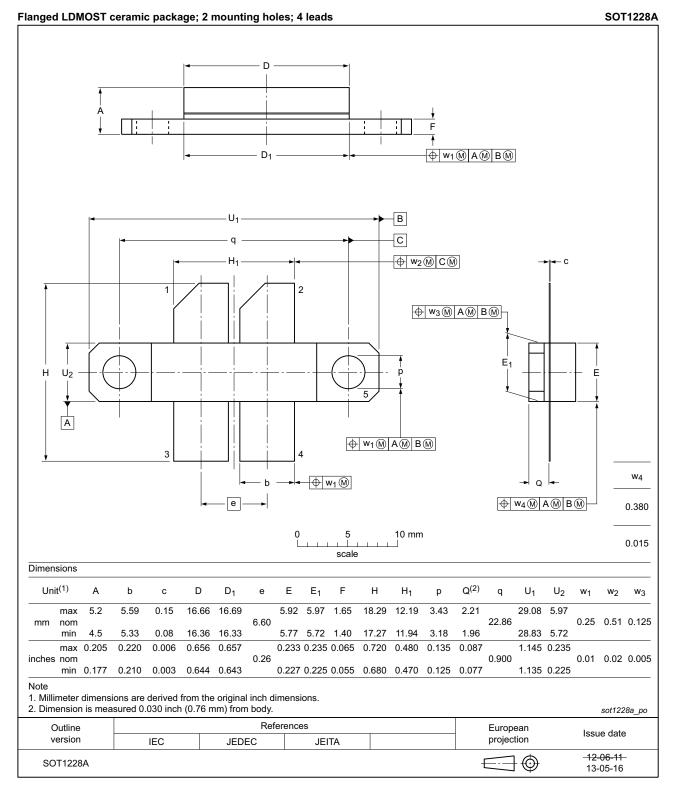
#### **Test information** 7.

### 7.1 Ruggedness in class-AB operation

The BLF644P is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V; f = 1300 MHz at rated load power.

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### 8. Package outline



#### Fig 1. Package outline SOT1228A

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## 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## **10. Abbreviations**

Table 9. Abbrevi	ations
Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
VSWR	Voltage Standing-Wave Ratio

## **11. Revision history**

Table 10. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF644P v.1	20130611	Objective data sheet	-	-	

## 12. Legal information

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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